

Technische Information / Technical Information

euppec

Netz-Thyristor
Phase Control Thyristor

T 509 N 12 ...18

N 

Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Periodische Vorwärts- und Rückwärts-Spitzenperrspannung repetitive peak forward and reverse voltages	$T_{vj} = -40^\circ C \dots T_{vj\max}$	V_{DRM}, V_{RRM}	1200 1600	1400 1800	V V ¹⁾
Vorwärts-Stoßspitzenperrspannung non-repetitive peak forward off-state voltage	$T_{vj} = -40^\circ C \dots T_{vj\max}$	V_{DSM}	1200 1600	1400 1800	V V
Rückwärts-Stoßspitzenperrspannung non-repetitive peak reverse voltage	$T_{vj} = +25^\circ C \dots T_{vj\max}$	V_{RSM}	1300 1700	1500 1900	V V
Durchlaßstrom-Grenzeffektivwert RMSM on-state current		I_{TRSMSM}		800	A
Dauergrenzstrom average on-state current	$T_C = 85^\circ C$	I_{TAVM}		508	A
Stoßstrom-Grenzwert surge current	$T_{vj} = 25^\circ C, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj\max}, t_p = 10 \text{ ms}$	I_{TSM}		8000 6900	A A
Grenzlastintegral I^2t -value	$T_{vj} = 25^\circ C, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj\max}, t_p = 10 \text{ ms}$	I^2t		320 238	$A^2s * 10^3$ $A^2s * 10^3$
Kritische Stromsteilheit critical rate of rise of on-state current	DIN IEC 747-6 $f=50 \text{ Hz}, v_L = 10 \text{ V}, i_{GM} = 1 \text{ A}$ $di_C/dt = 1 \text{ A}/\mu\text{s}$	$(di_T/dt)_{cr}$		120	$\text{A}/\mu\text{s}$
Kritische Spannungssteilheit critical rate of rise of off-state voltage	$T_{vj} = T_{vj\max}, v_D = 0,67 V_{DRM}$ 5.Kennbuchstabe / 5th letter F	$(dv_D/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$

Charakteristische Werte / Characteristic values

Durchlaßspannung on-state voltage	$T_{vj} = T_{vj\max}, i_T = 1600 \text{ A}$	v_T	max.	1,92	V
Schleusenspannung threshold voltage	$T_{vj} = T_{vj\max}$	$v_{T(TO)}$		0,8	V
Ersatzwiderstand slope resistance	$T_{vj} = T_{vj\max}$	r_T		0,6	$\text{m}\Omega$
Durchlaßkennlinie on-state voltage $v_T = A + B \times i_T + C \times \ln(i_T + 1) + D \times \sqrt{i_T}$	$T_{vj} = T_{vj\max}$	$A=0,93854$ $B=3,384E-04$ $C=-5,551E-02$ $D=2,001E-02$			
Zündstrom gate trigger current	$T_{vj} = 25^\circ C, v_D = 6 \text{ V}$	I_{GT}	max.	200	mA
Zündspannung gate trigger voltage	$T_{vj} = 25^\circ C, v_D = 6 \text{ V}$	v_{GT}	max.	2	V
Nicht zündener Steuerstrom gate non-trigger current	$T_{vj} = T_{vj\max}, v_D = 6 \text{ V}$ $T_{vj} = T_{vj\max}, v_D = 0,5 V_{DRM}$	I_{GD}	max.	10	mA
Nicht zündene Steuerspannung gate non-trigger voltage	$T_{vj} = T_{vj\max}, v_D = 0,5 V_{DRM}$	v_{GD}	max.	0,2	mV
Haltestrom holding current	$T_{vj} = 25^\circ C, v_D = 6 \text{ V}, R_A = 5 \Omega$	I_H	max.	300	mA
Einraststrom latching current	$T_{vj} = 25^\circ C, v_D = 6 \text{ V}, R_{GK}=10 \Omega$ $i_{GM} = 1 \text{ A}, di_C/dt = 1 \text{ A}/\mu\text{s}$ $t_g = 20 \mu\text{s}$	I_L	max.	1200	mA
Vorwärts- und Rückwärts-Sperrstrom forward off-state and reverse currents	$T_{vj} = T_{vj\max}$ $v_D = V_{DRM}, v_R = V_{RRM}$	i_D, i_R	max.	50	mA
Zündverzug gate controlled delay time	DIN IEC 747-6 $T_{vj} = 25^\circ C$ $i_{GM} = 1 \text{ A}, di_C/dt = 1 \text{ A}/\mu\text{s}$	t_{gd}	max.	4	μs

1) 1800 V auf Anfrage / 1800 V on demand

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Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

Freiwerdezeit circuit commutation turn-off time	$T_{vj} = T_{vj \max}, i_{TM}=I_{TAVM}$ $V_{RM} = 100V, V_{DM} = 0,67 V_{DRM}$ $dv_D/dt = 20 V/\mu s, -di_T/dt = 10 A/\mu s$ 4. Kennbuchstabe / 4th letter O	t_q	typ.	250	μs
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Thermische Eigenschaften / Thermal properties

Innerer Wärmewiderstand thermal resistance, junction to case	Kühlfläche / cooling surface beidseitig / two-sided, $\theta = 180^\circ \sin$ Anode / anode, $\theta = 180^\circ \sin$ Kathode / cathode, $\theta = 180^\circ \sin$	R_{thJC}	max. 0,0530 max. 0,0500 max. 0,0880 max. 0,0850 max. 0,1230 max. 0,1200	$^{\circ}C/W$ $^{\circ}C/W$ $^{\circ}C/W$ $^{\circ}C/W$ $^{\circ}C/W$ $^{\circ}C/W$
Übergangs- Wärmewiderstand thermal resistance, case to heatsink	Kühlfläche / cooling surface beidseitig / two-sided einseitig / single-sided	R_{thCK}	max. 0,0075 max. 0,0150	$^{\circ}C/W$ $^{\circ}C/W$
Höchstzulässige Sperrsichttemperatur max. junction temperature		$T_{vj \ max}$	125	$^{\circ}C$
Betriebstemperatur operating temperature		$T_{c \ op}$	-40...125	$^{\circ}C$
Lagertemperatur storage temperature		T_{stg}	-40...140	$^{\circ}C$

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see appendix			Seite 3 page 3	
Si-Element mit Druckkontakt Si-pellet with pressure contact				
Anpreßkraft clamping force		F	5 ...10	kN
Gewicht weight		G	typ. 270	g
Kriechstrecke creepage distance			28	mm
Feuchteklassierung humidity classification	DIN 40040		C	
Schwingfestigkeit vibration resistance	f = 50Hz		50	m/s ²

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen./ The technical Information specifies semiconductors devices but promises no characteristics. It is valid in combination with the belonging technical notes.

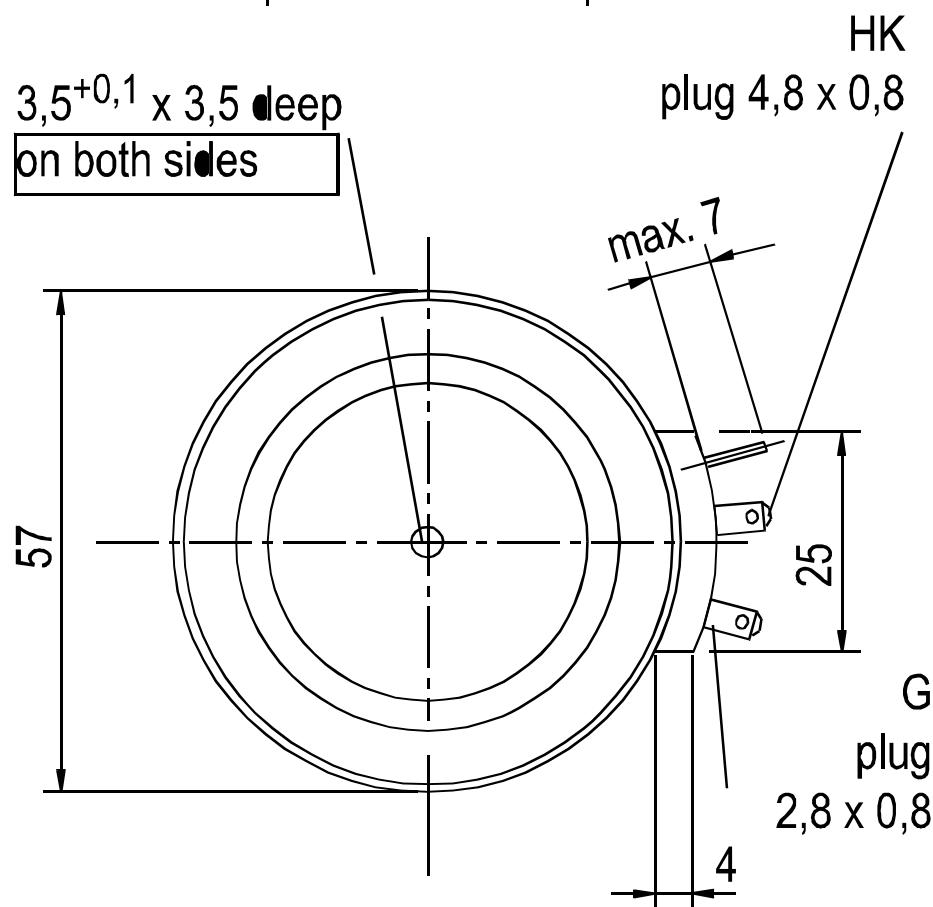
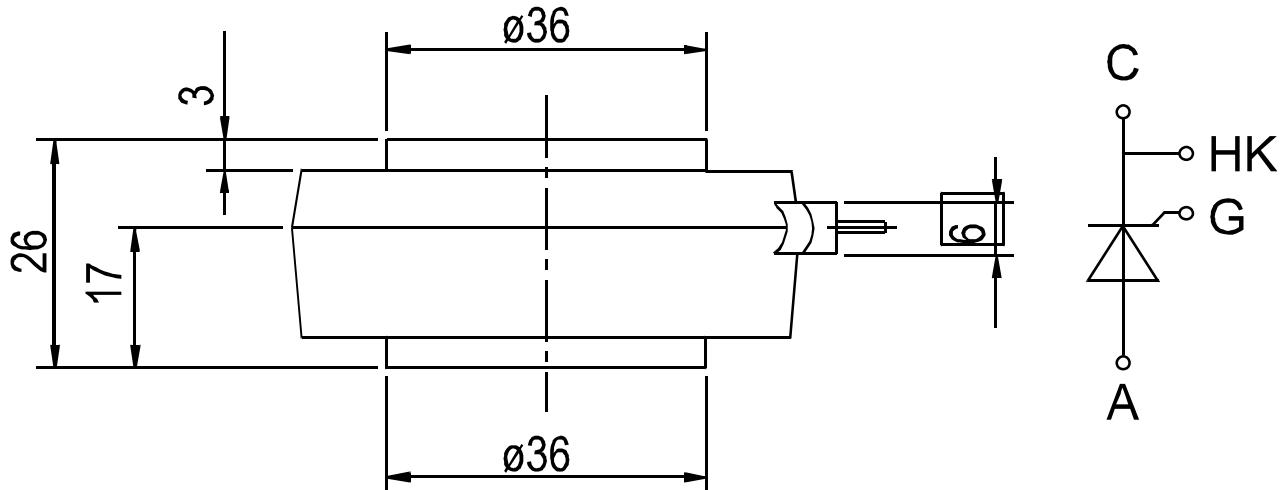
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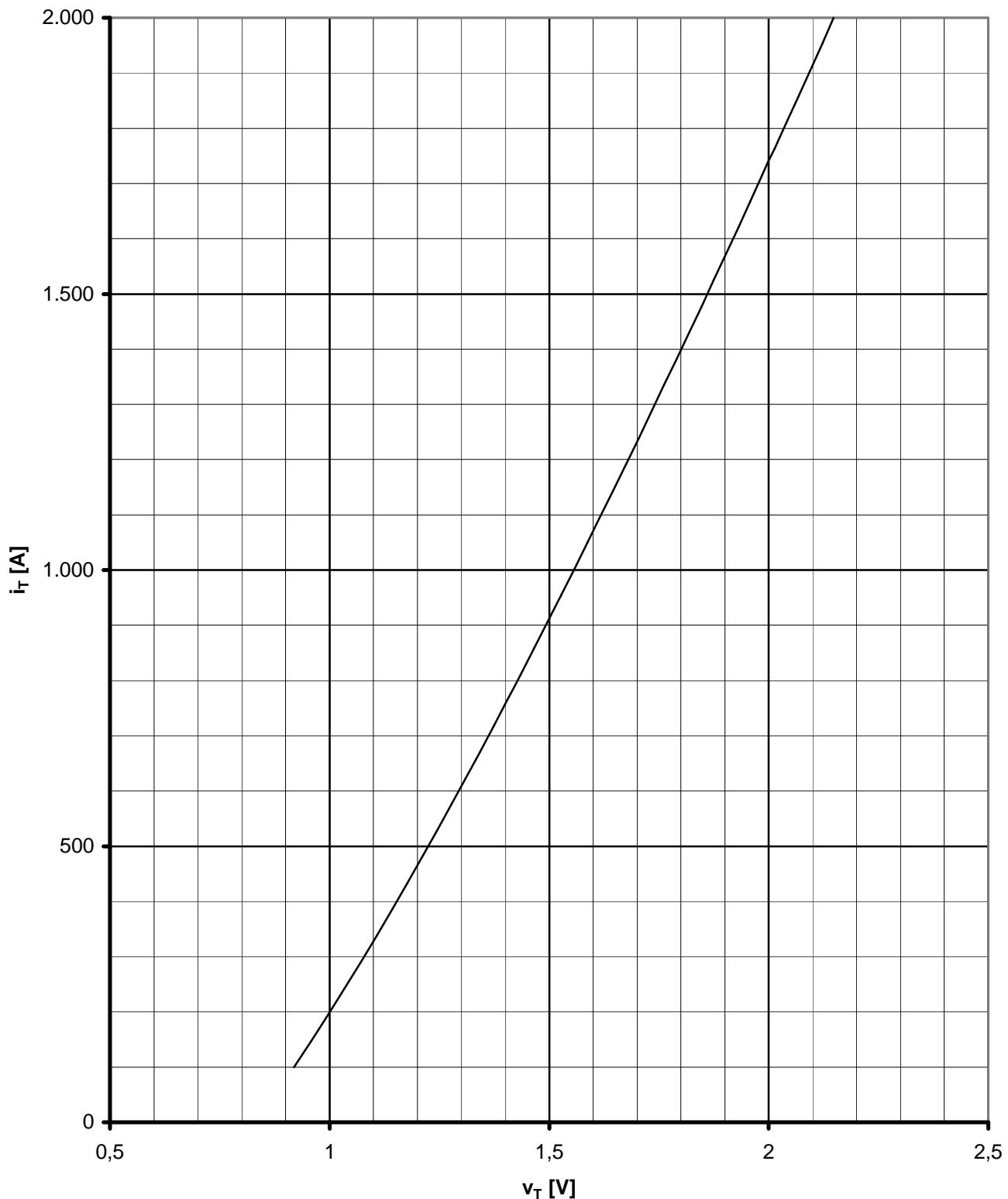
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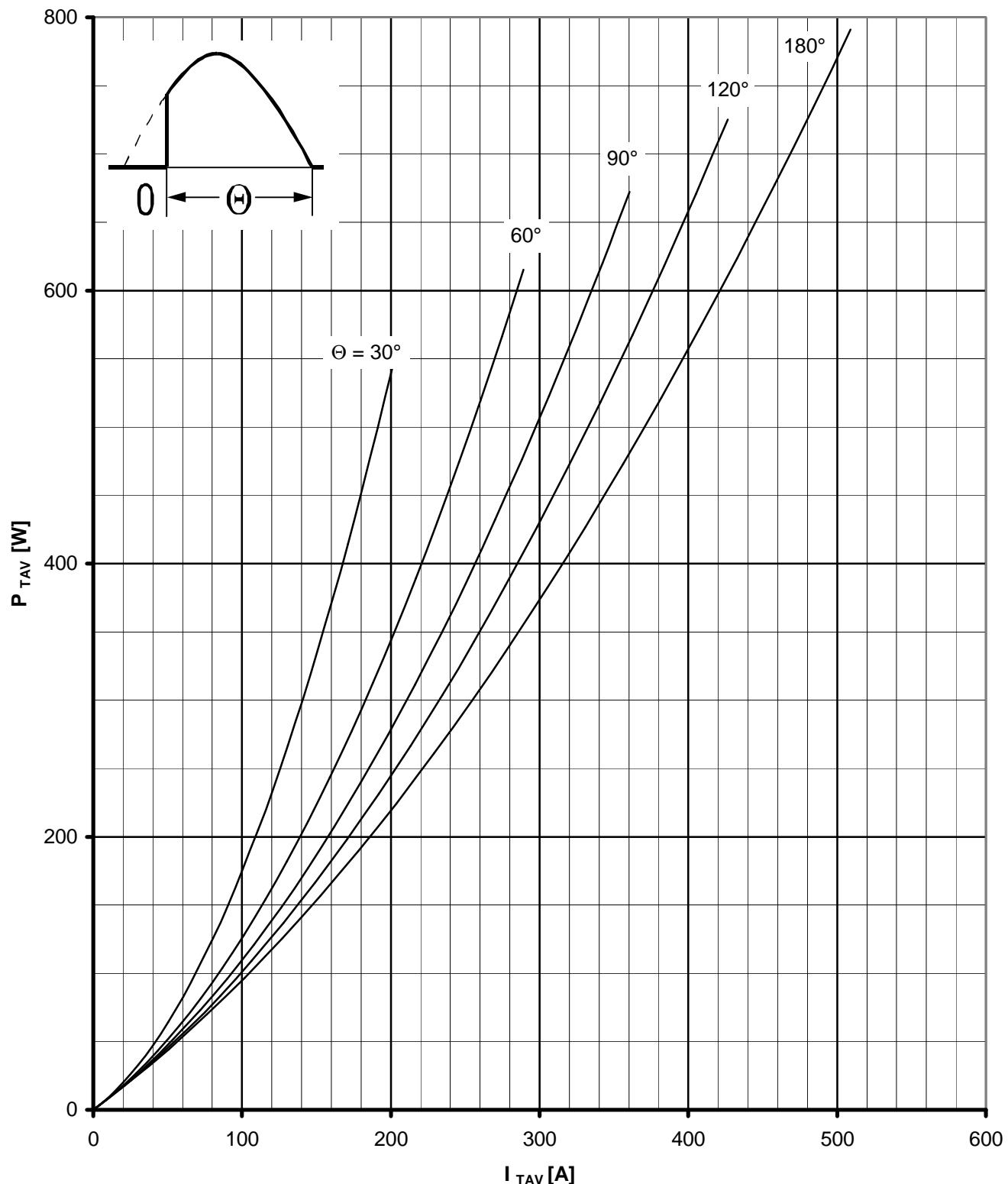
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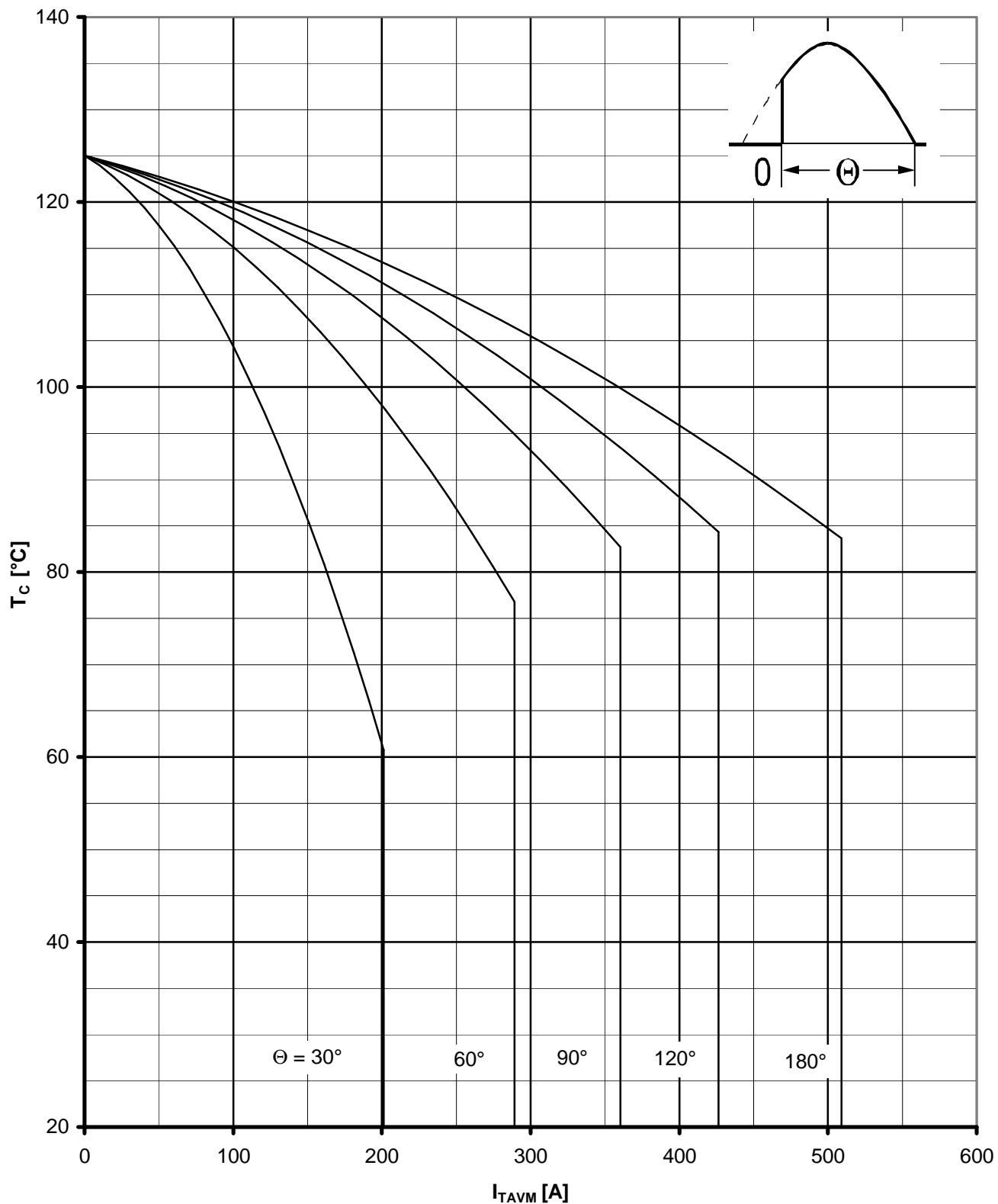


Kühlung cooling	Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} für DC Analytical elements of transient thermal impedance Z_{thJC} for DC							
	Pos.n	1	2	3	4	5	6	7
beidseitig two-sided	R_{thn} [°C/W]	0,010500	0,002830	0,016700	0,018800	0,001160		
	τ_n [s]	0,001130	0,025500	0,051100	0,429000	2,490000		
anodenseitig anode-sided	R_{thn} [°C/W]	0,009400	0,009740	0,018200	0,016100	0,031600		
	τ_n [s]	0,000984	0,016700	0,204000	0,821000	5,000000		
kathodenseitig cathode-sided	R_{thn} [°C/W]	0,009280	0,014500	0,008680	0,040100	0,047500		
	τ_n [s]	0,000939	0,028500	0,156000	1,120000	9,100000		
Analytische Funktion / analytical function : $Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} (1 - \text{EXP} (- t / \tau_n))$								

Grenzdurchlaßkennlinie / Limiting On-state characteristics $i_T = f(v_T)$ $T_{vj} = T_{vj\ max}$

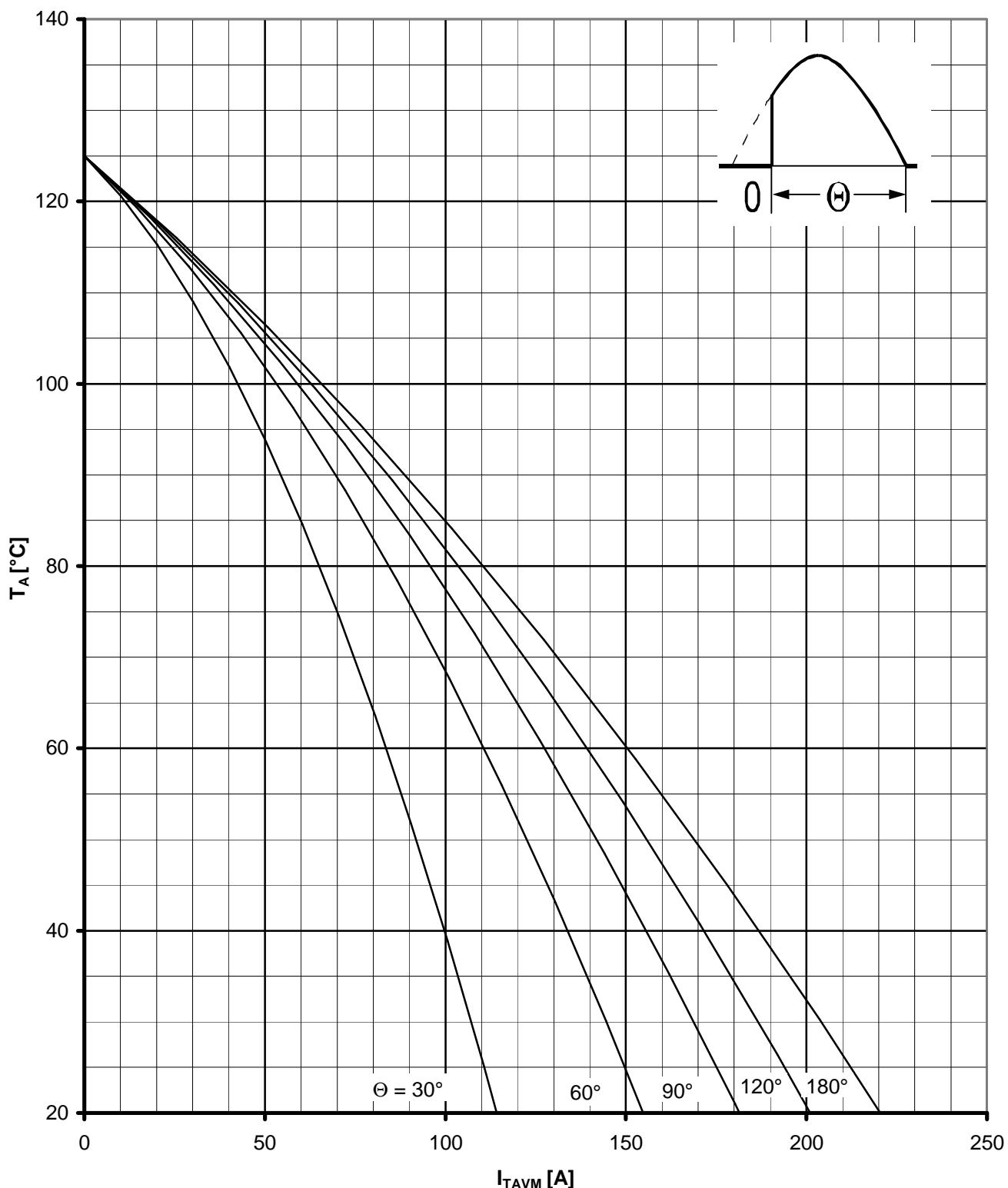


Durchlaßverlustleistung / On-state power loss $P_{TAV} = f(I_{TAV})$
Parameter: Stromflußwinkel Θ / current conduction angle Θ

Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_c = f(I_{TAVM})$

Beidseitige Kühlung / Two-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ

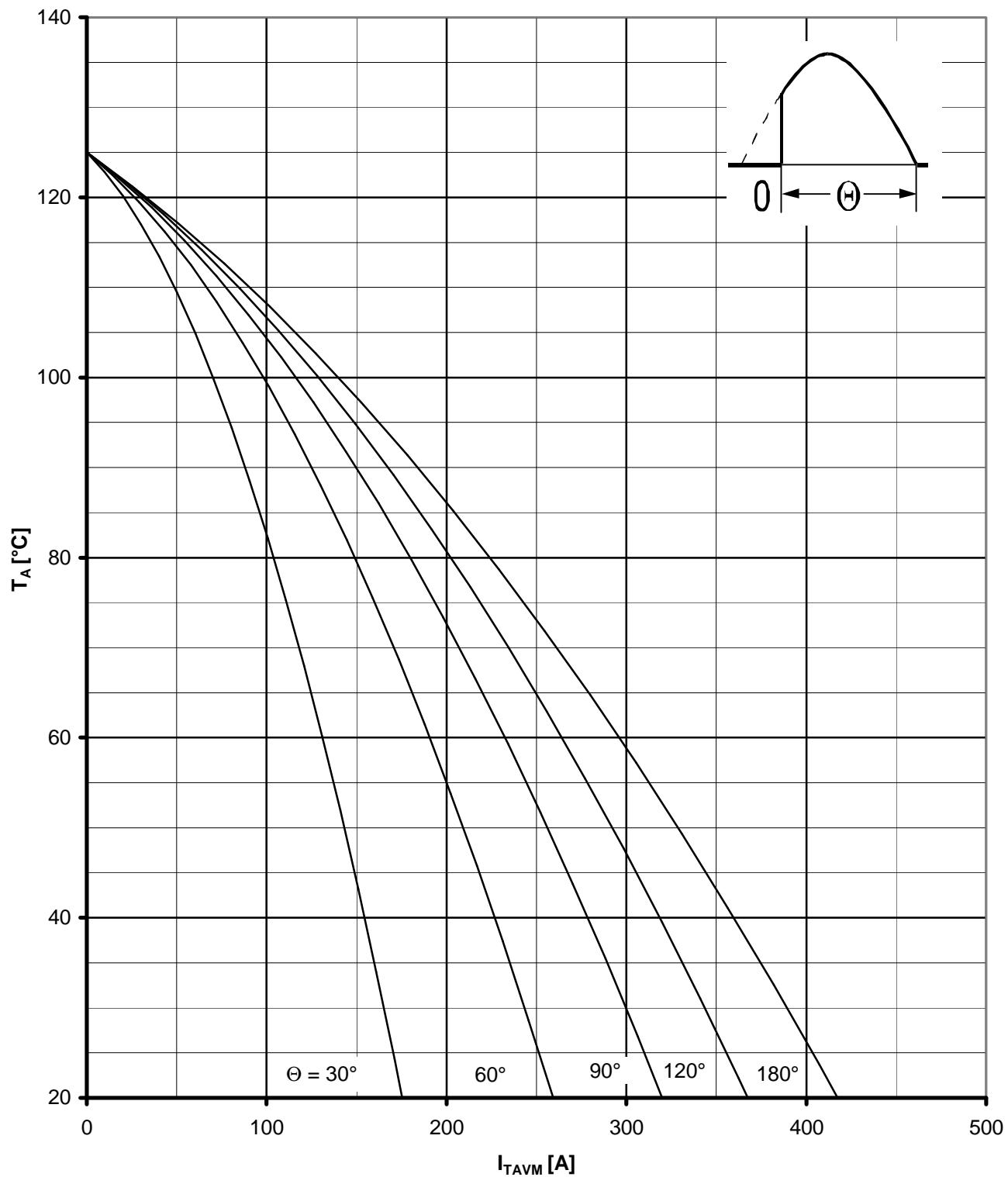


Höchstzulässige Kühlmitteltemperatur / Max. allowable cooling medium temperature $T_A = f(I_{TAVM})$

Luftselbstkühlung / Natural air-cooling

Kühlkörper/Heatsink. K0.36S

Parameter: Stromflußwinkel Θ / current conduction angle Θ

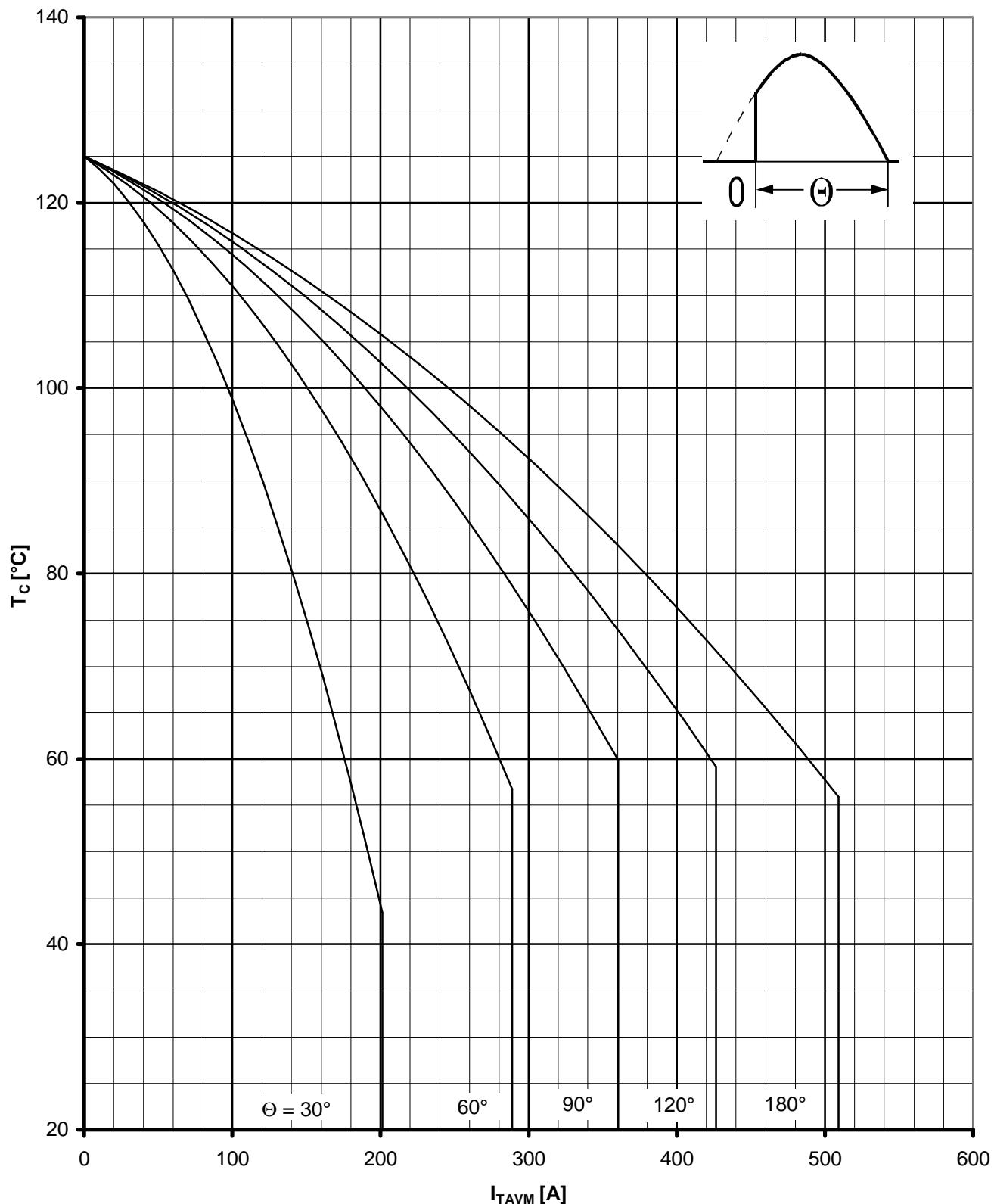


Höchstzulässige Kühlmitteltemperatur / Max. allowable cooling medium temperature $T_A = f(I_{TAVM})$

Verstärkte Luftkühlung / Forced air-cooling

Kühlkörper/Heatsink. K0.05F, $V_L = 50$ l/s

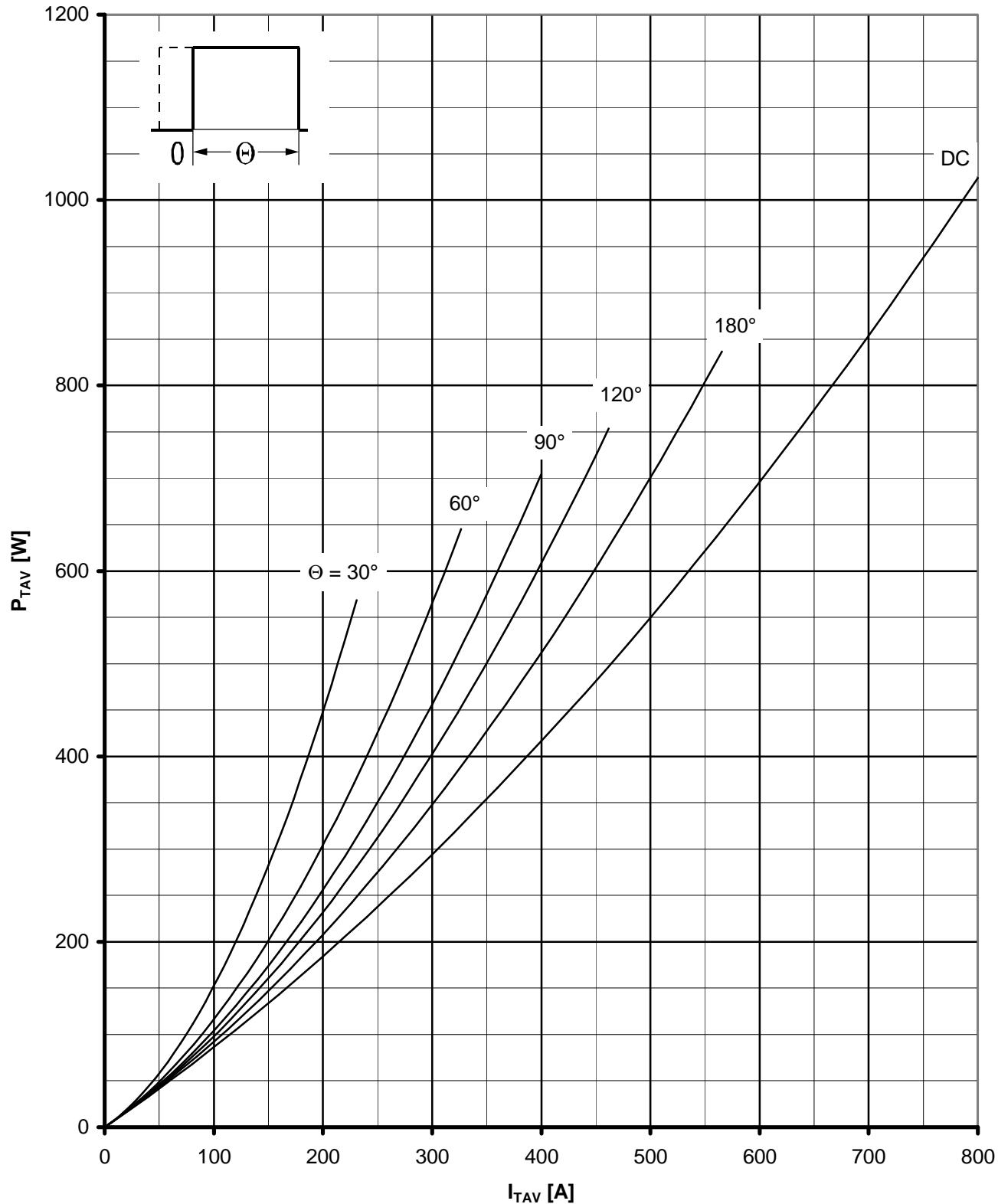
Parameter: Stromflußwinkel Θ / current conduction angle Θ



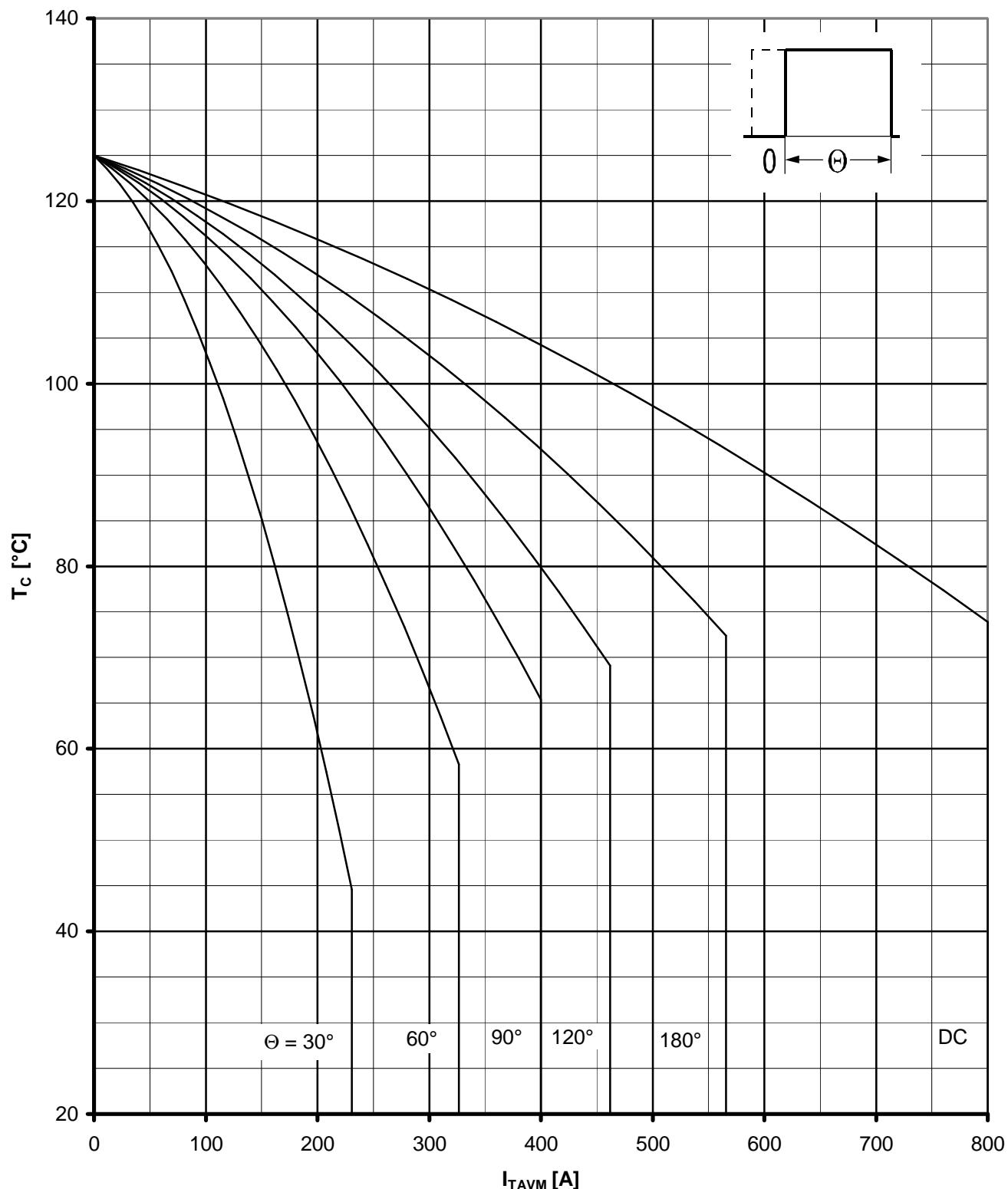
Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_c = f(I_{TAVM})$

Anodenseitige Kühlung / anode sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ

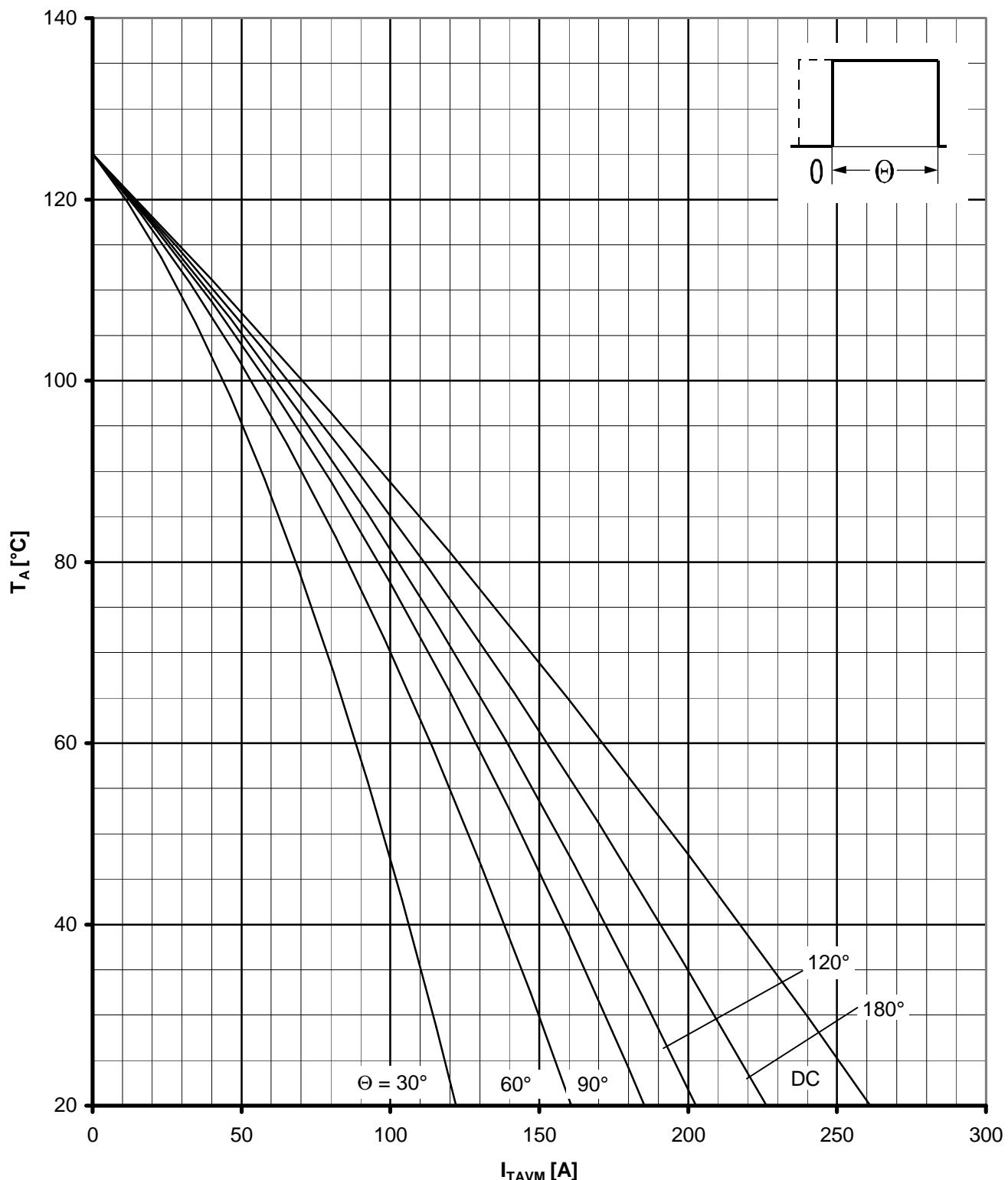


Durchlaßverlustleistung / On-state power loss $P_{TAV} = f(I_{TAV})$
Parameter: Stromflußwinkel Θ / current conduction angle Θ

Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_c = f(I_{TAVM})$

Beidseitige Kühlung / Two-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ

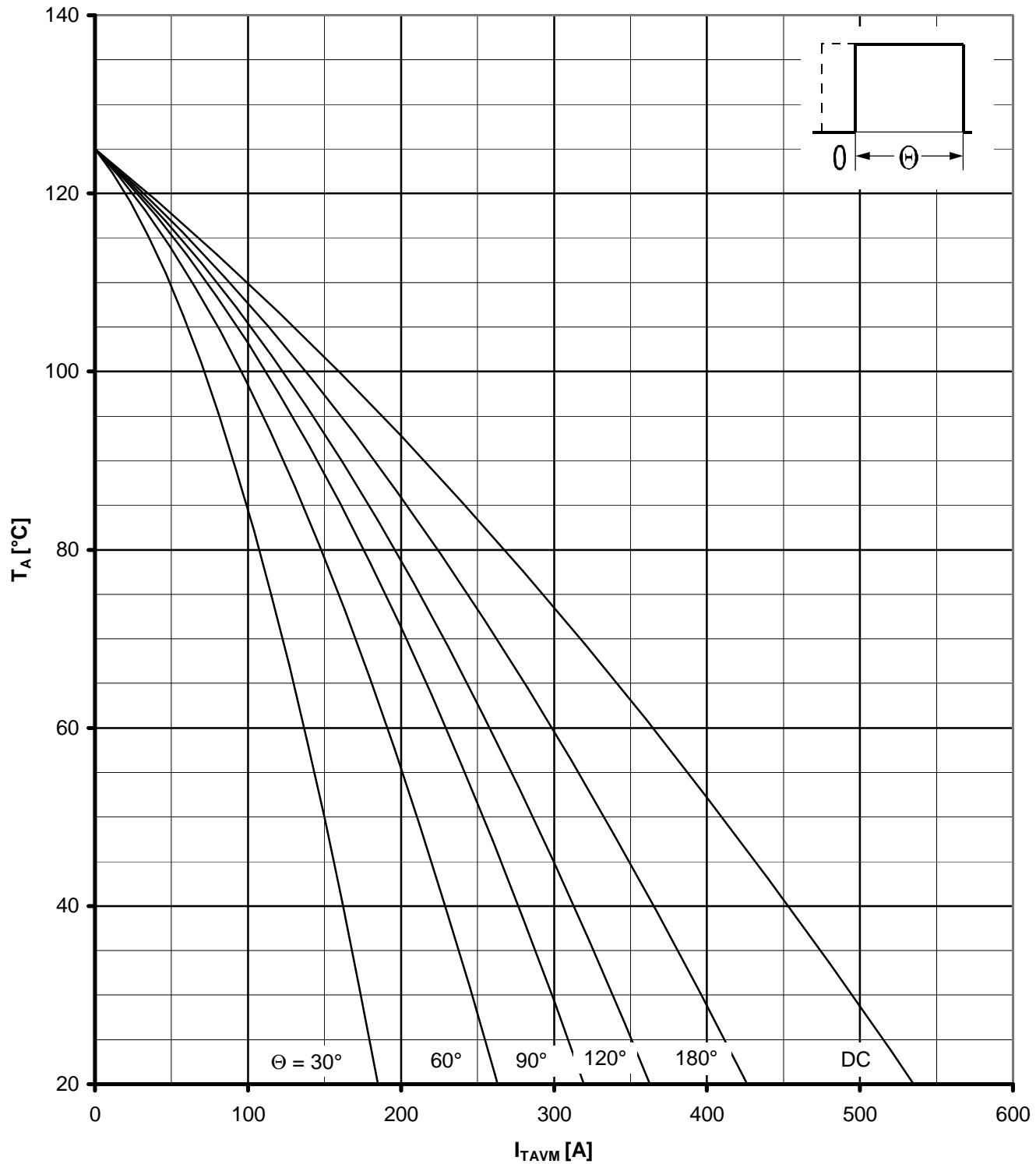


Höchstzulässige Kühlmitteltemperatur / Max. allowable cooling medium temperature $T_A = f(I_{TAVM})$

Luftselbstkühlung / Natural air-cooling

Kühlkörper/Heatsink. K 0.36 S

Parameter: Stromflußwinkel Θ / current conduction angle Θ

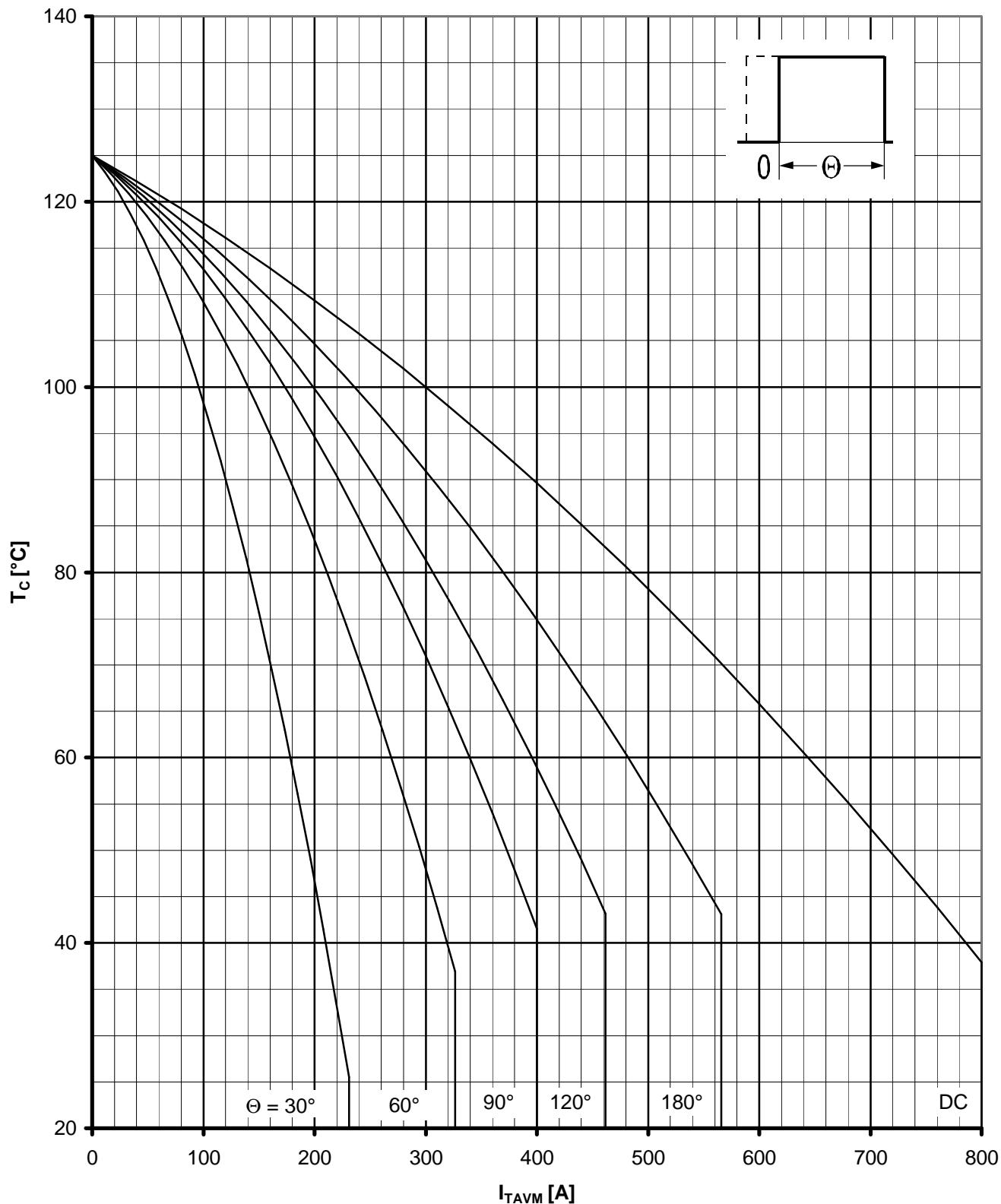


Höchstzulässige Kühlmitteltemperatur / Max. allowable cooling medium temperature $T_A = f(I_{TAVM})$

Verstärkte Luftkühlung / Forced air-cooling

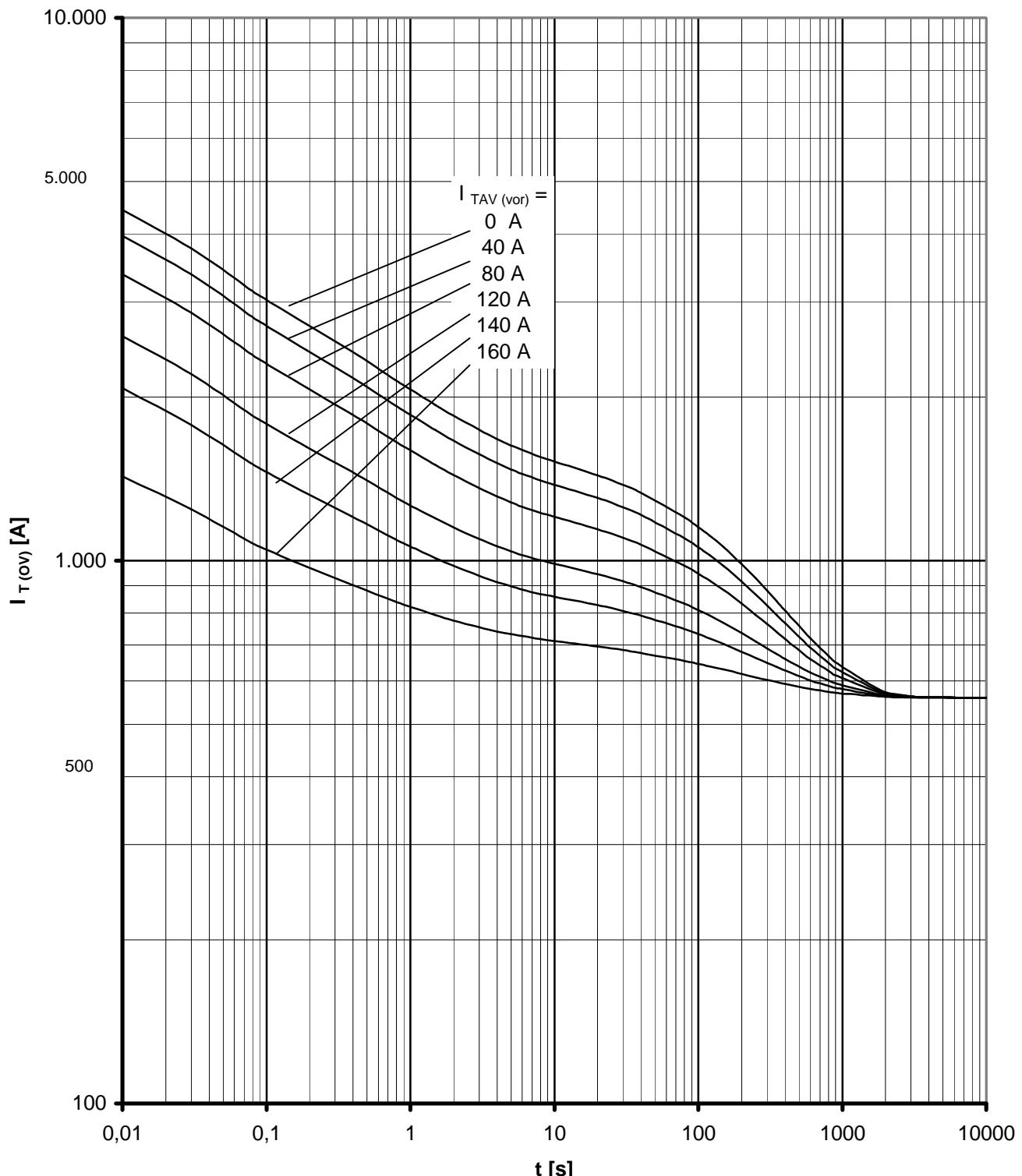
Kühlkörper/Heatsink. K0.05F, $V_L = 50$ l/s

Parameter: Stromflußwinkel Θ / current conduction angle Θ

Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_c = f(I_{TAVM})$

Anodenseitige Kühlung / anode sided cooling

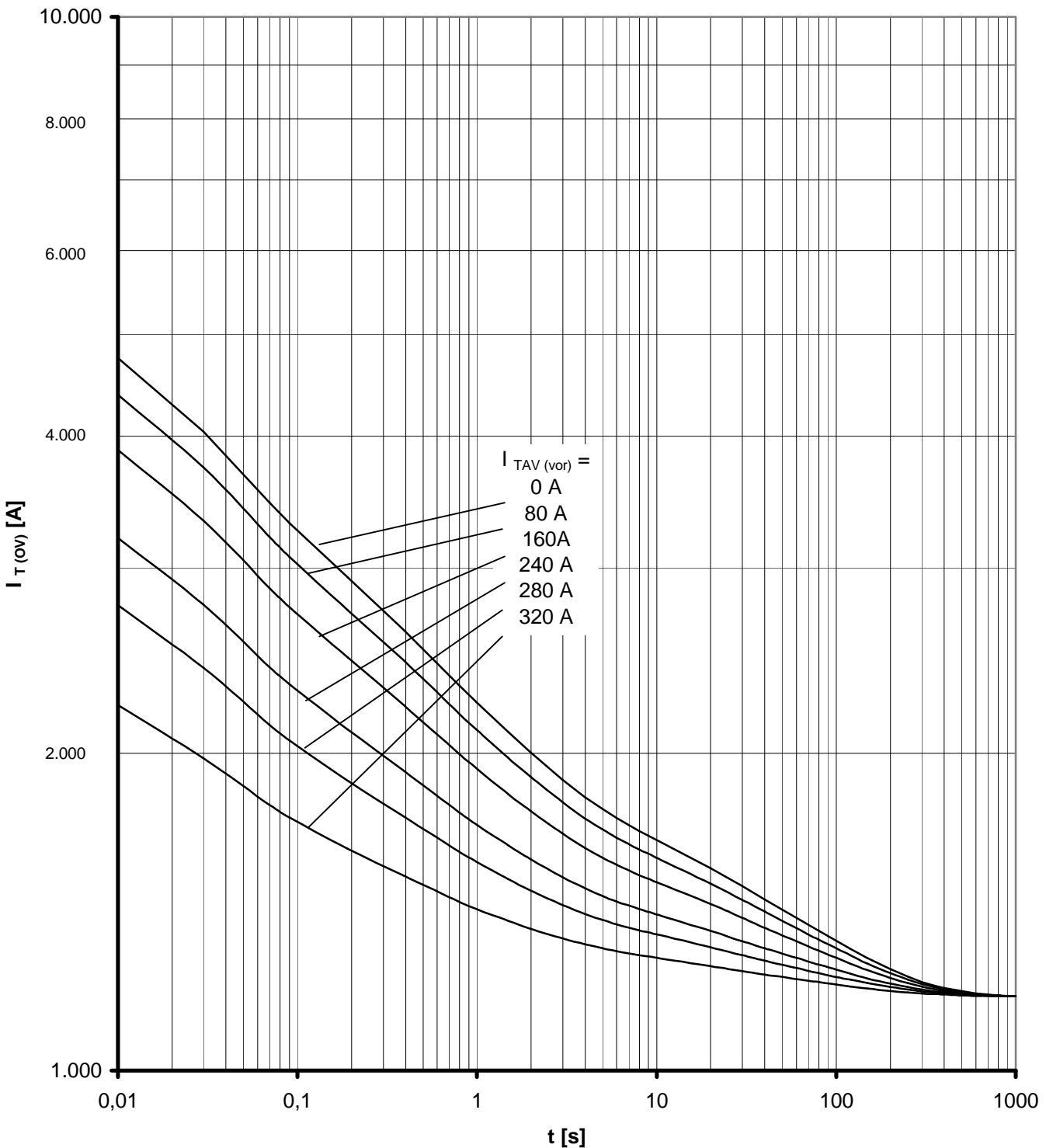
Parameter: Stromflußwinkel Θ / current conduction angle Θ



Überstrom / Overload on-state current $I_{T(OV)} = f(t)$

Beidseitige Luftsselfkühlung / Two-sided natural cooling K 0.36 S
 $T_A = 45^\circ\text{C}$

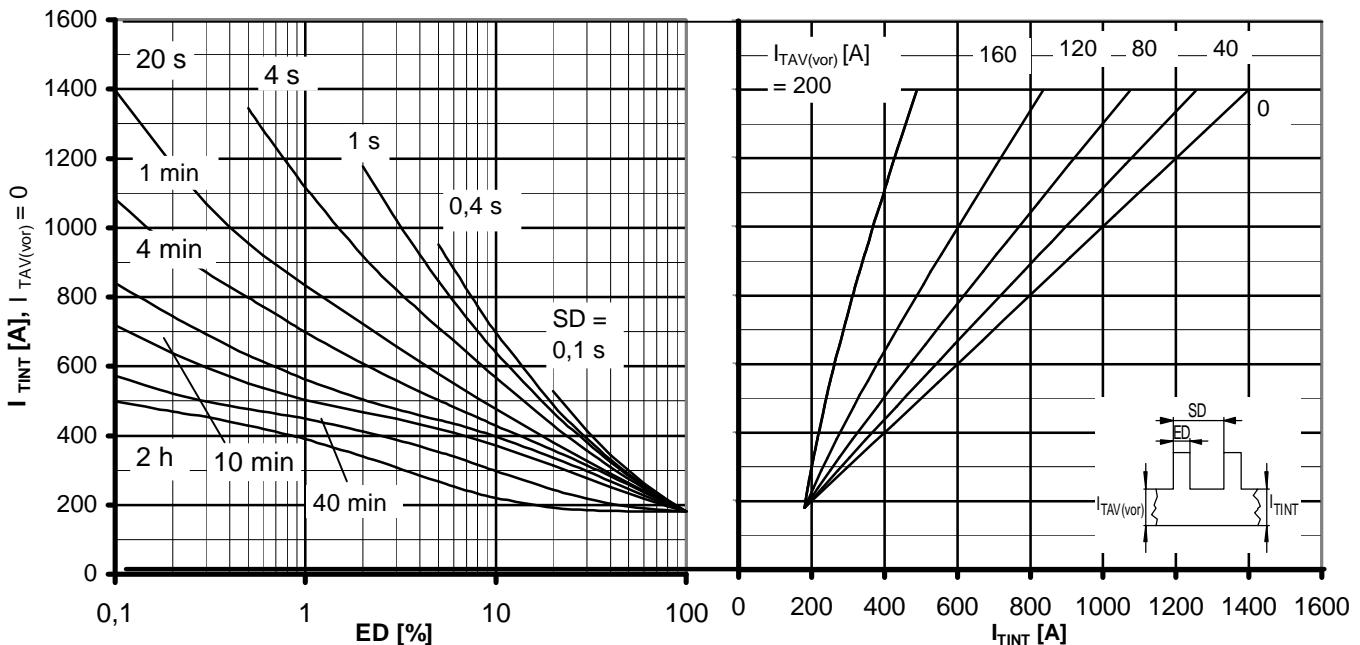
Parameter: Vorlaststrom / pre-load current $I_{TAV(vor)}$



Überstrom / Overload on-state current $I_{T(OV)} = f(t)$

Beidseitige verstärkte Kühlung / forced two-sided cooling K0.12F
 $T_A = 35^\circ\text{C}$, $V_L = 50 \text{ l/s}$

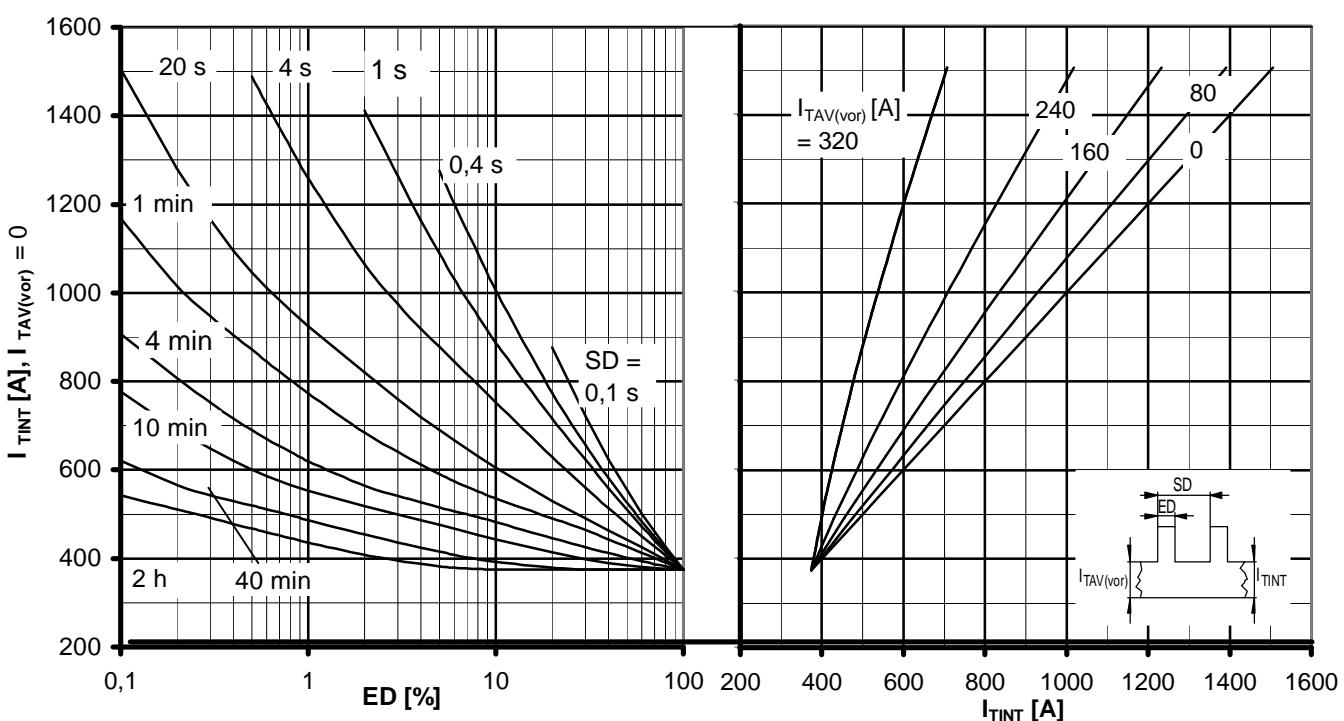
Parameter: Vorlaststrom / pre-load current $I_{TAV(vor)}$



Höchstzul. Durchlaßstrom bei Aussetzbetrieb / Max. allowable on-state current during intermittent operation $I_{TINT} = f(ED)$

Beidseitig Luftsselfst Kühlung / two-sided natural cooling K 0.05F
 $T_A = 45^\circ C$

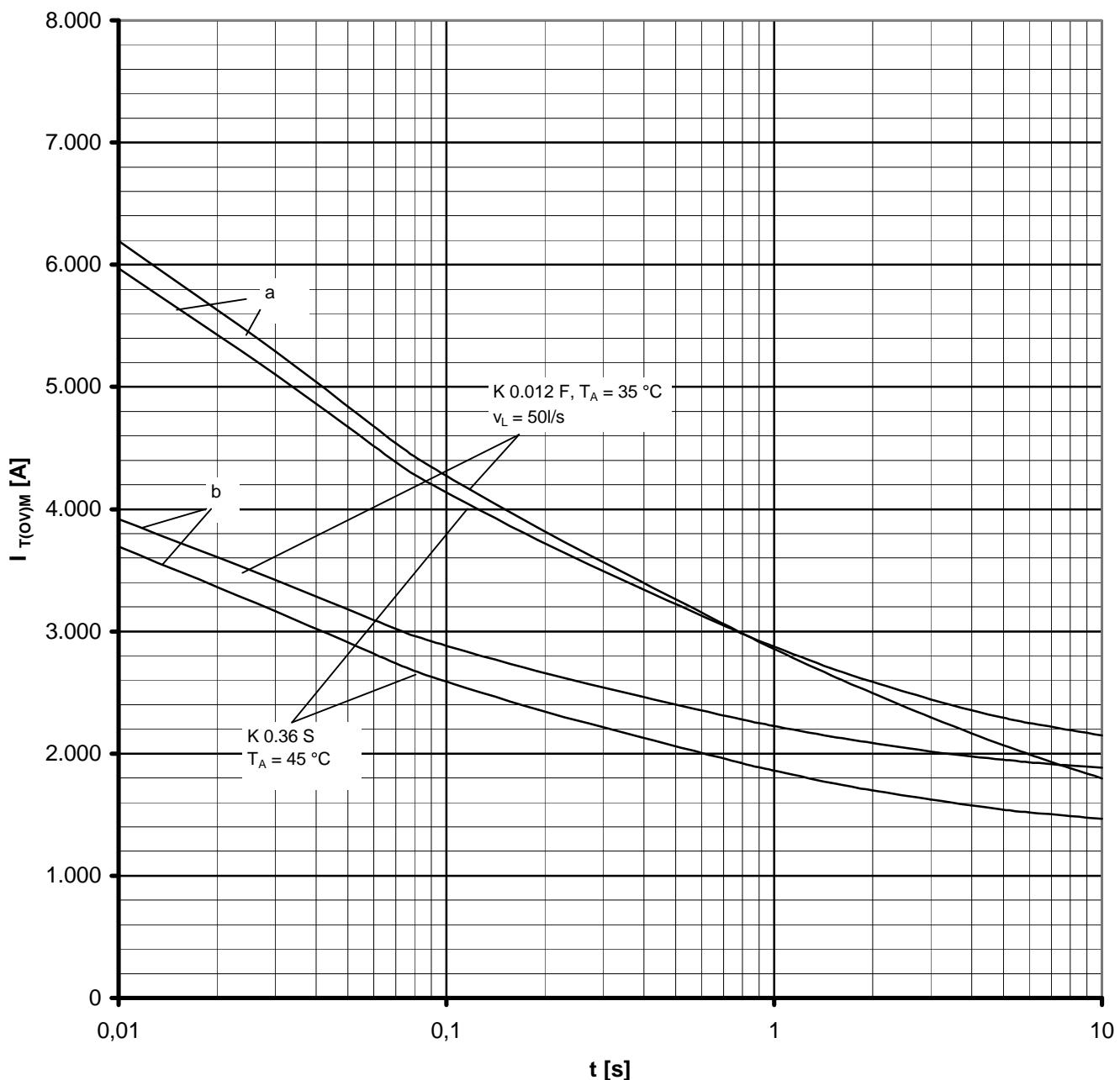
Parameter: Vorlaststrom / pre-load current $I_{TAV(vor)}$, Spieldauer / cycle duration SD



Höchstzul. Durchlaßstrom bei Aussetzbetrieb / Max. allowable on-state current during intermittent operation $I_{TINT} = f(ED)$

Beidseitig verstärkte Kühlung / forced two-sided cooling K 0.05F
 $T_A = 35^\circ C$, $V_L = 120$ l/s

Parameter: Vorlaststrom / pre-load current $I_{TAV(vor)}$, Spieldauer / cycle duration SD



Grenzstrom / Max. overload on-state current $I_{T(OV)M} = f(t)$, $v_{RM} = 0,8 V_{RRM}$

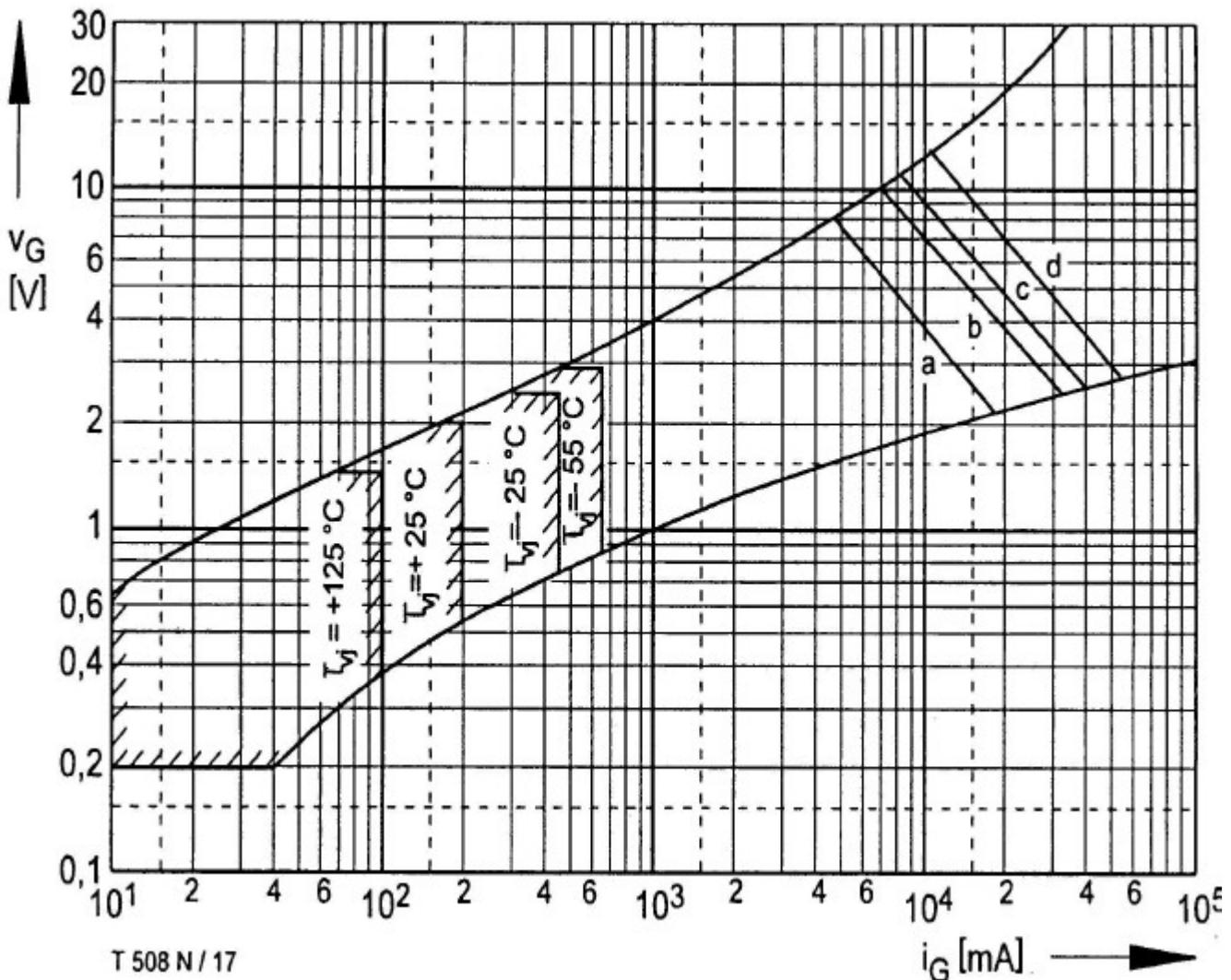
Beidseitige Kühlung / Two-sided cooling

Kühlkörper / Heatsink: K0.36S, K 0.05F

Belastung aus / Surge current occurs:

a - Leerlauf / No-load conditions

b - Betrieb mit Dauergrenzstrom / During operation at max. average on-state current I_{TAVM}

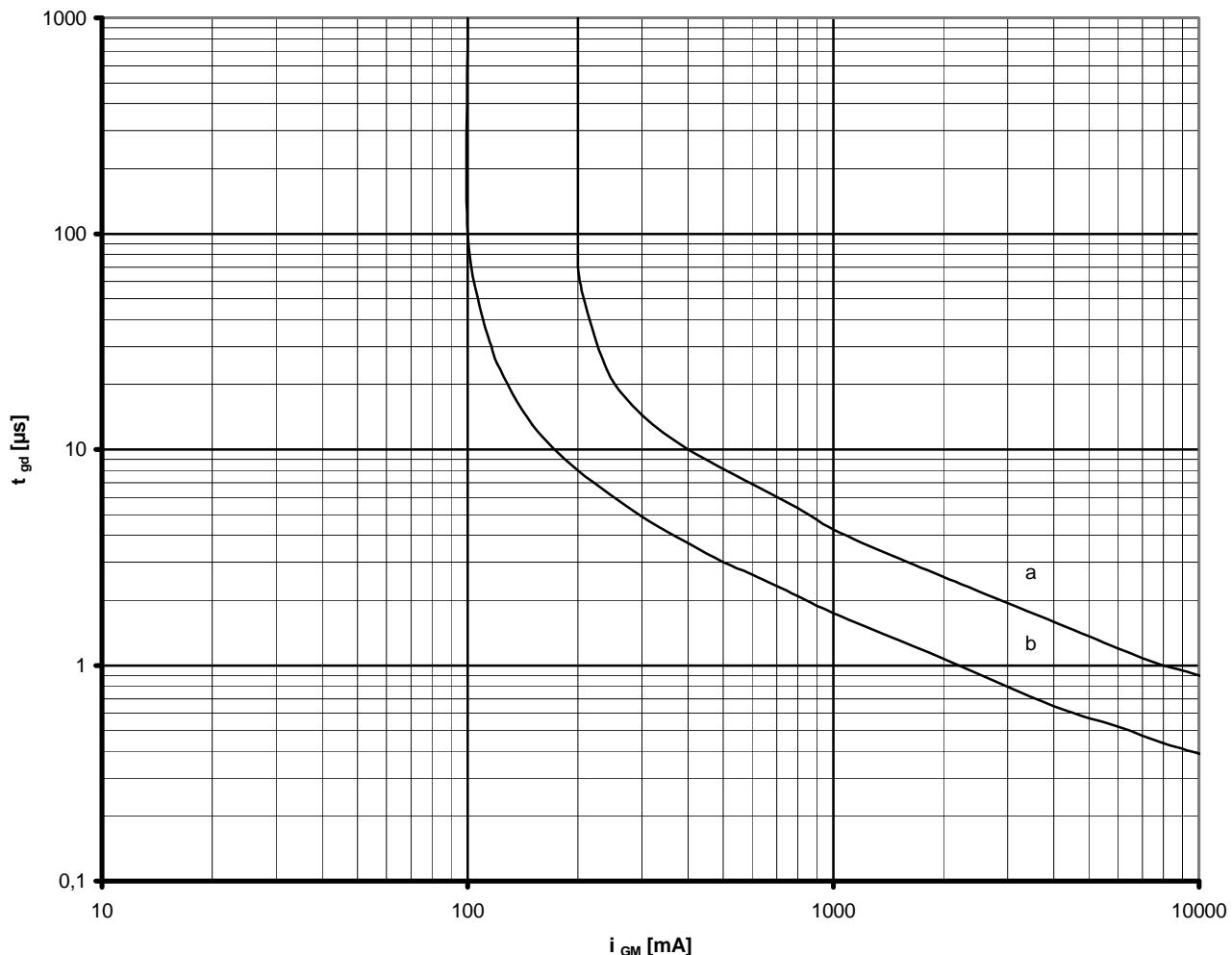


Steuercharakteristik $v_G = f(i_G)$ mit Zündbereichen für $V_D = 6$ V

Gate characteristic $v_G = f(i_G)$ with triggering area for $V_D = 6$ V

Höchstzulässige Spitzensteuerverlustleistung / Maximum rated peak gate power dissipation $P_{GM} = f(t_g)$:

a - 40 W/10ms b - 80 W/1ms c - 100 W/0,5ms d - 150 W/0,1ms

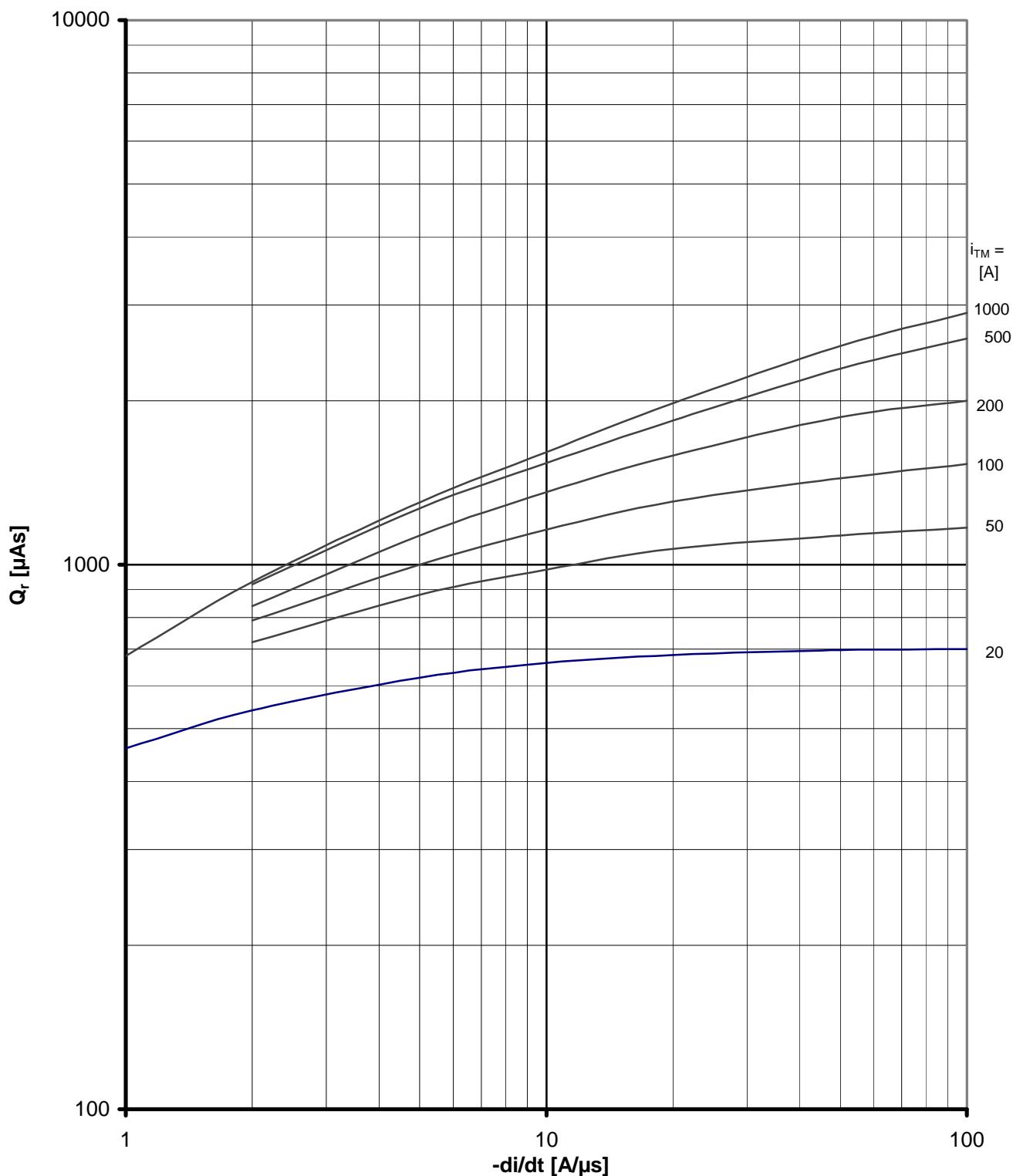


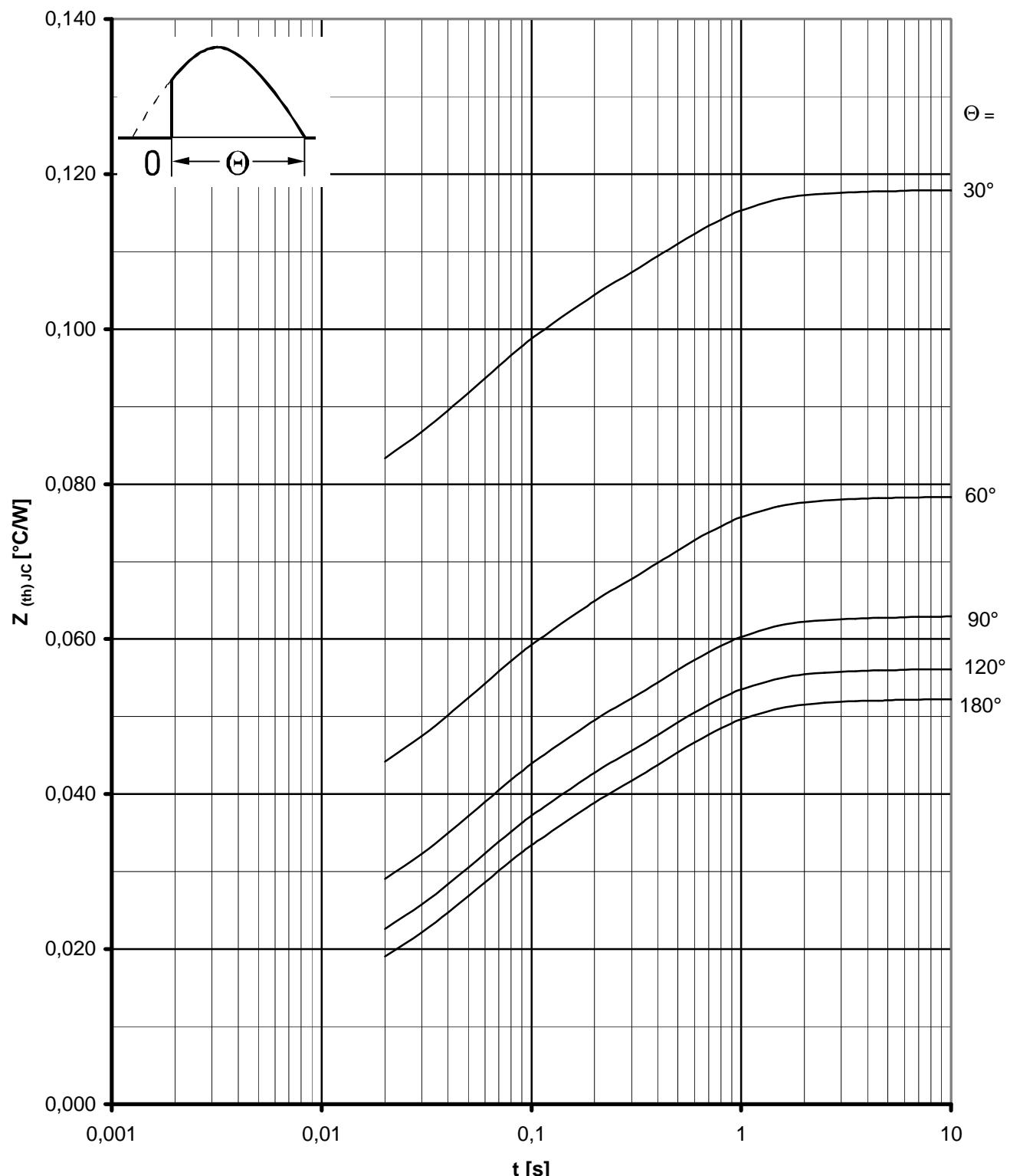
Zündverzug / Gate controlled delay time $t_{gd} = f(i_{GM})$

$T_{vj} = 25^\circ\text{C}$, $di_G/dt = i_{GM}/1\mu\text{s}$

a - maximaler Verlauf / limiting characteristic

b - typischer Verlauf / typical characteristic

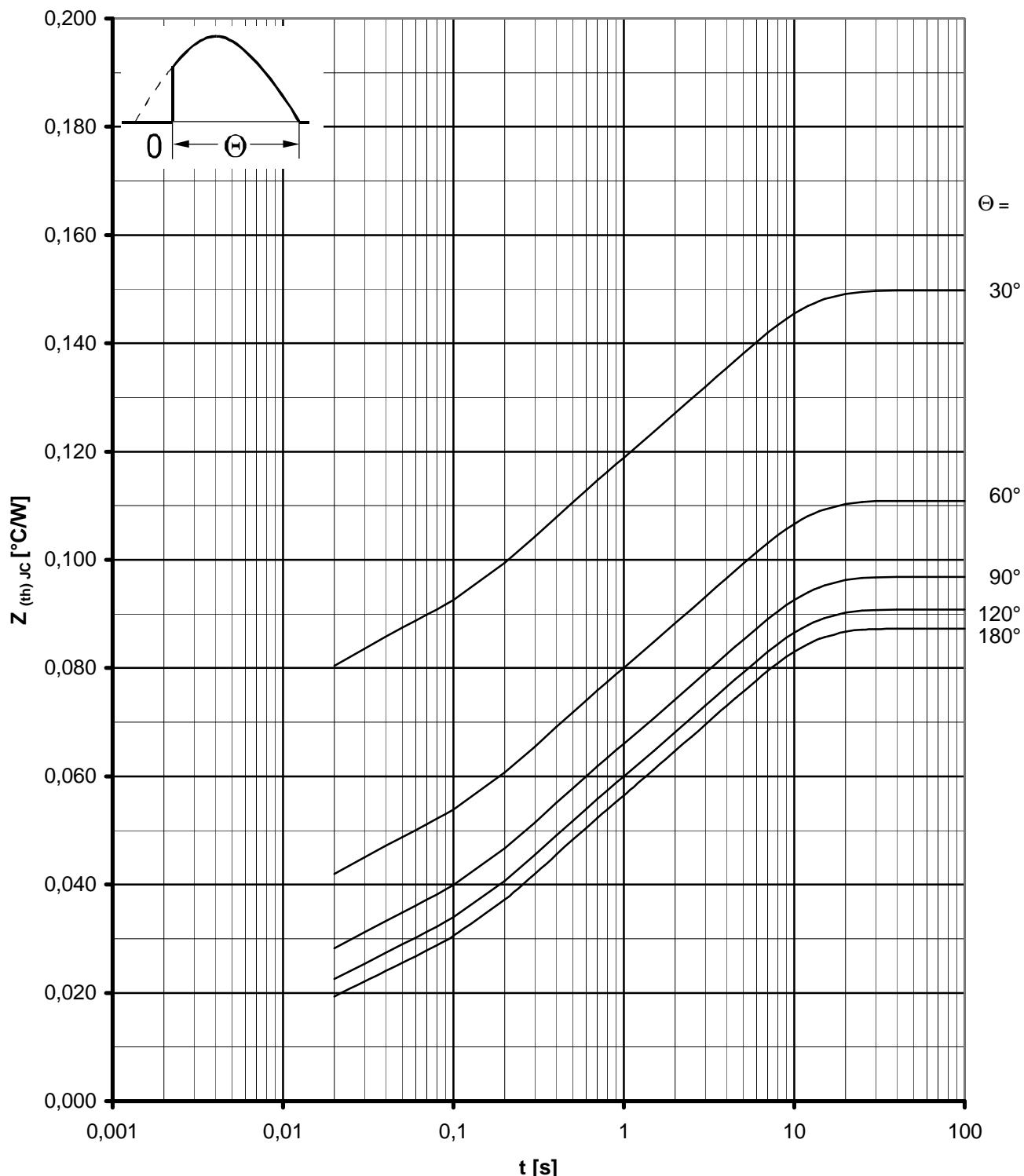
Sperrverzögerungsladung / Recovered charge $Q_r = f(di/dt)$ $T_{vj} = T_{vj \max}$, $v_R = 0,5 V_{RRM}$, $v_{RM} = 0,8 V_{RRM}$ Parameter: Durchlaßstrom / On-state current i_{TM}



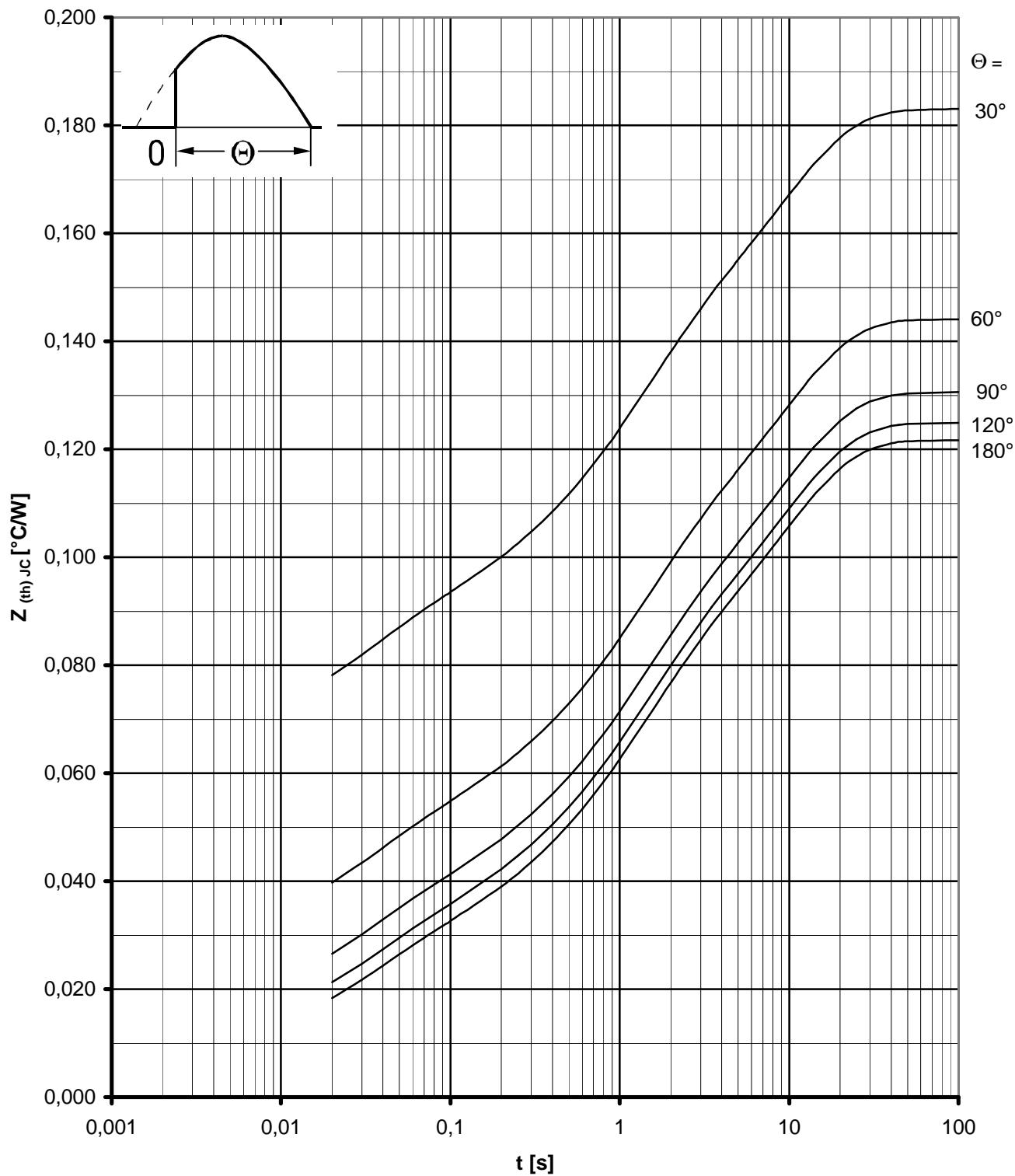
Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$

Beidseitige Kühlung / Two-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ

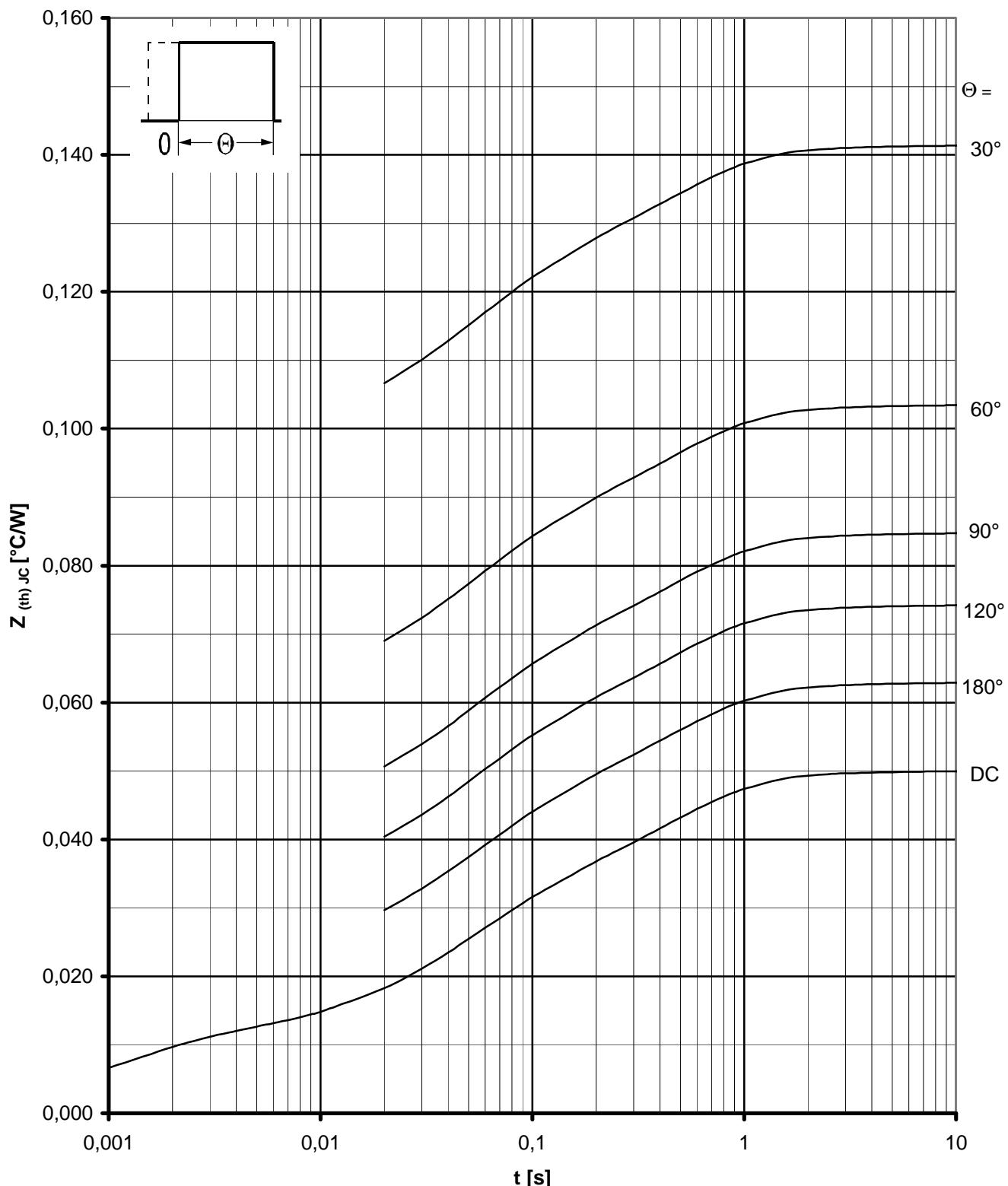
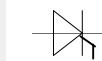


Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$
Anodenseitige Kühlung / Anode-sided cooling
Parameter: Stromflußwinkel Θ / current conduction angle Θ

Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$

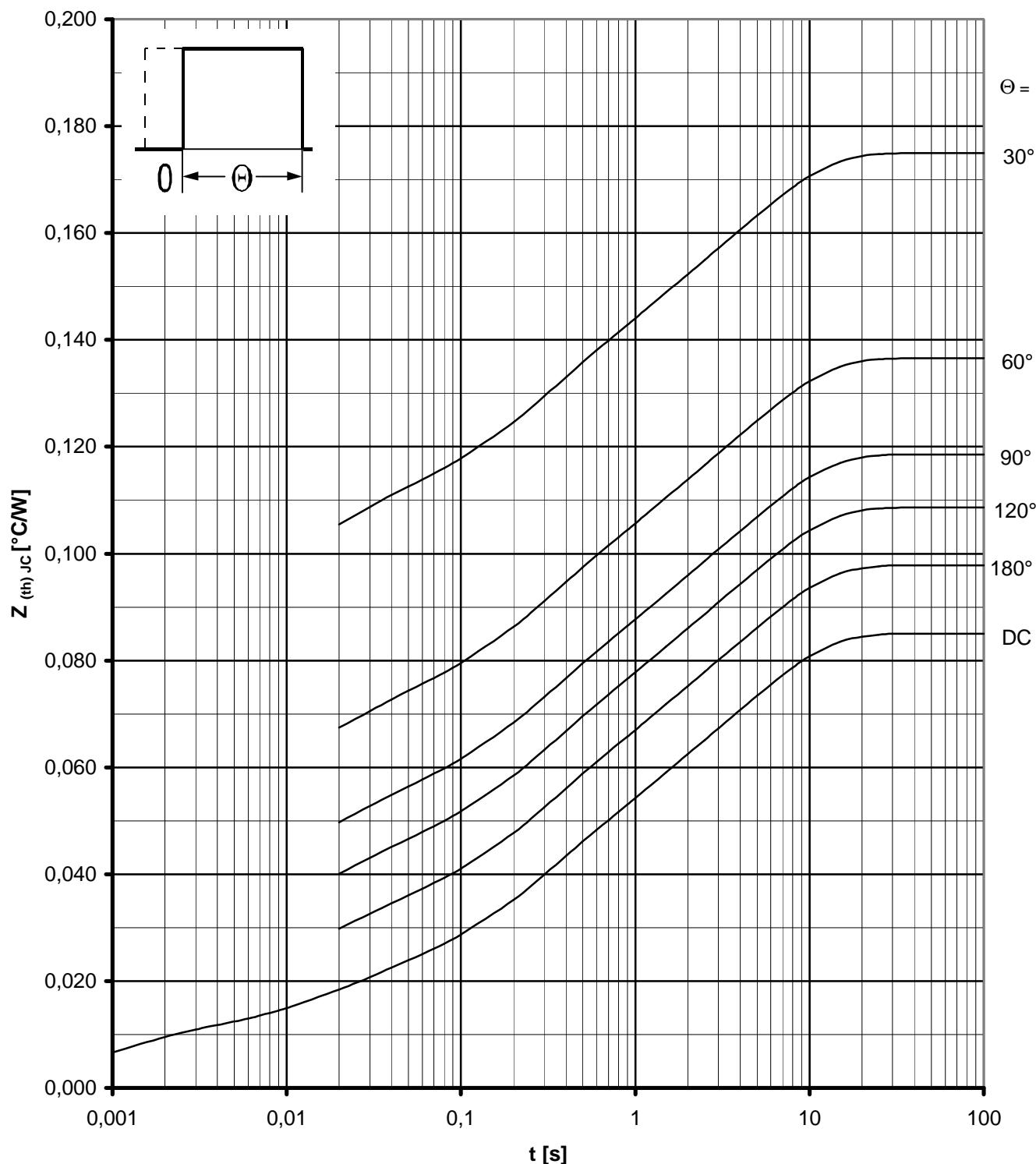
Kathodenseitige Kühlung / Cathode-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ

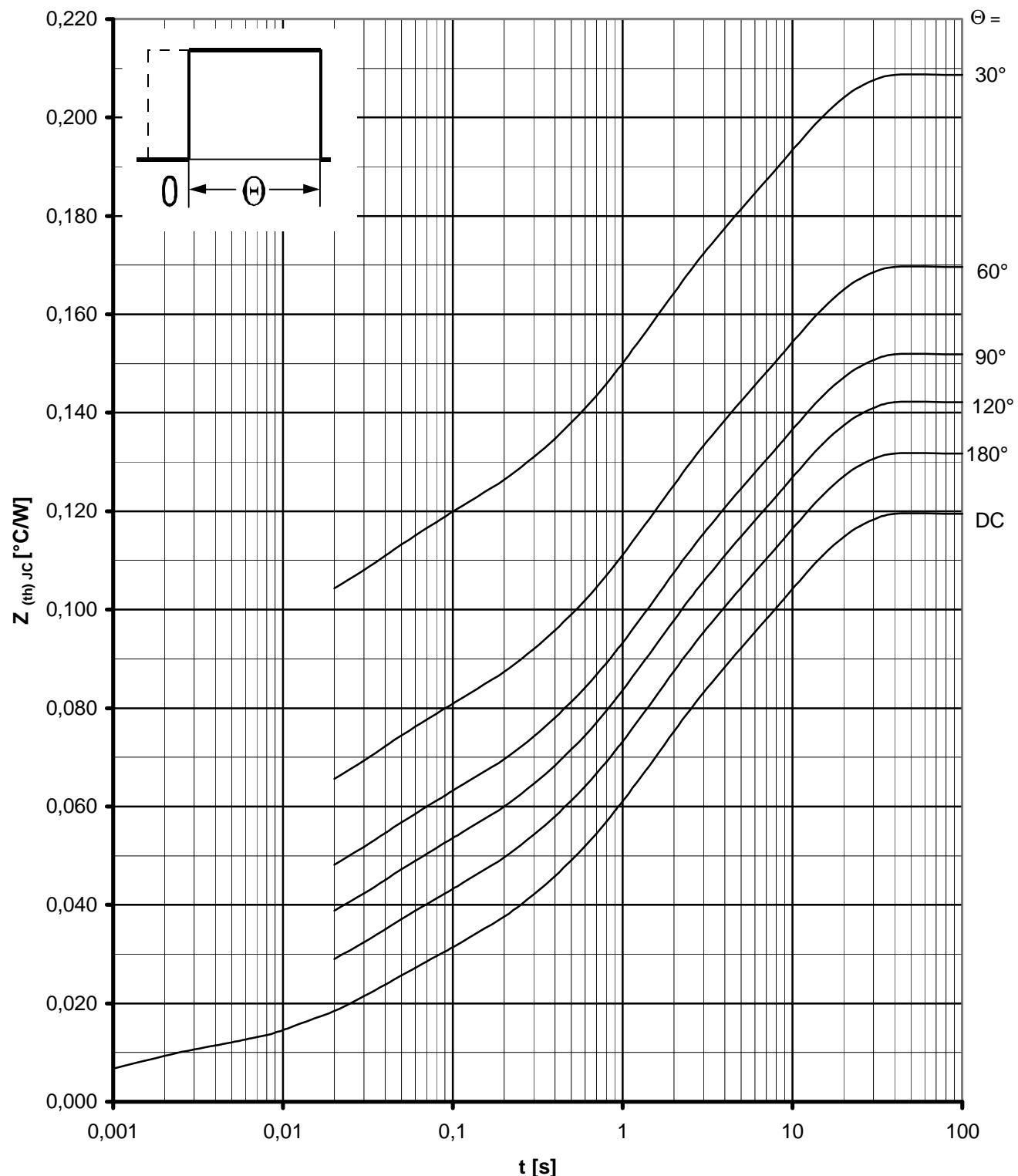
Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$

Beidseitige Kühlung / Two-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ



Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$
 Anodenseitige Kühlung / Anode-sided cooling
 Parameter: Stromflußwinkel Θ / current conduction angle Θ



Transienter innerer Wärmewiderstand / Transient thermal impedance $Z_{(th)JC} = f(t)$

Kathodenseitige Kühlung / Cathode-sided cooling

Parameter: Stromflußwinkel Θ / current conduction angle Θ